

ABSTRACT

In one aspect, provided is an etchant that is able to reduce the deposition and adhesion of silica, which is produced in an etching process, on a silicon oxide film.

An aspect of the present disclosure relates to an etchant for a process of removing a silicon nitride film from a substrate having a silicon nitride film and a silicon oxide film. The etchant contains a siloxane compound modified with a compound having an alkyleneoxy group, a phosphoric acid, and water.